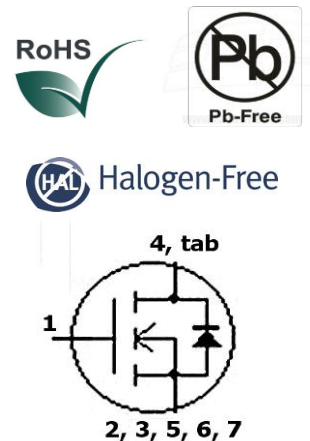


**OptiMOS™ Power-Transistor**
**Features**

- Optimized for synchronous rectification
- 100% avalanche tested
- Superior thermal resistance
- N-channel, normal level
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

**Product Summary**

$V_{DS}$	60	V
$R_{DS(on),max}$	1.0	mΩ
$I_D$	180	A
$Q_{oss}$	228	nC
$Q_G(0V..10V)$	208	nC



Type	IPB010N06N
Package	TO263-7
Marking	010N06N

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}, T_C=25\text{ °C}$	180	A
		$V_{GS}=10\text{ V}, T_C=100\text{ °C}$	180	
		$V_{GS}=10\text{ V}, T_C=25\text{ °C}, R_{thJA}=40\text{ K/W}^2)$	45	
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	720	
Avalanche energy, single pulse <sup>4)</sup>	$E_{AS}$	$I_D=100\text{ A}, R_{GS}=25\text{ Ω}$	1600	mJ
Gate source voltage	$V_{GS}$		±20	V

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See figure 3 for more detailed information

<sup>4)</sup> See figure 13 for more detailed information

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	$P_{\text{tot}}$	$T_C=25\text{ °C}$	300	W
Operating and storage temperature	$T_j, T_{\text{stg}}$		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{\text{thJC}}$		-	-	0.5	K/W
Device on PCB	$R_{\text{thJA}}$	minimal footprint	-	-	62	
		6 cm <sup>2</sup> cooling area <sup>2)</sup>	-	-	40	

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$	60	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=280\text{ }\mu\text{A}$	2.1	2.8	3.3	
Zero gate voltage drain current	$I_{\text{DSS}}$	$V_{\text{DS}}=60\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$	-	0.5	1	$\mu\text{A}$
		$V_{\text{DS}}=60\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	$I_{\text{GSS}}$	$V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=100\text{ A}$	-	0.8	1.0	m $\Omega$
		$V_{\text{GS}}=6\text{ V}, I_{\text{D}}=25\text{ A}$	-	1.0	1.5	
Gate resistance	$R_{\text{G}}$		-	1.8	2.7	$\Omega$
Transconductance	$g_{\text{fs}}$	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}, I_{\text{D}}=100\text{ A}$	160	310	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=30\text{ V}, f=1\text{ MHz}$	-	15000	18750	pF
Output capacitance	$C_{oss}$		-	3400	4250	
Reverse transfer capacitance	$C_{rss}$		-	130	260	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=30\text{ V}, V_{GS}=10\text{ V}, I_D=100\text{ A}, R_{G,ext}=3\ \Omega$	-	37	-	ns
Rise time	$t_r$		-	36	-	
Turn-off delay time	$t_{d(off)}$		-	74	-	
Fall time	$t_f$		-	23	-	

**Gate Charge Characteristics<sup>5)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=30\text{ V}, I_D=100\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	65	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	46	-	
Gate to drain charge	$Q_{gd}$		-	37	49	
Switching charge	$Q_{sw}$		-	56	-	
Gate charge total	$Q_g$		-	208	243	
Gate plateau voltage	$V_{plateau}$		-	4.2	-	V
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V}, V_{GS}=0\text{ to }10\text{ V}$	-	184	-	nC
Output charge	$Q_{oss}$	$V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$	-	228	-	

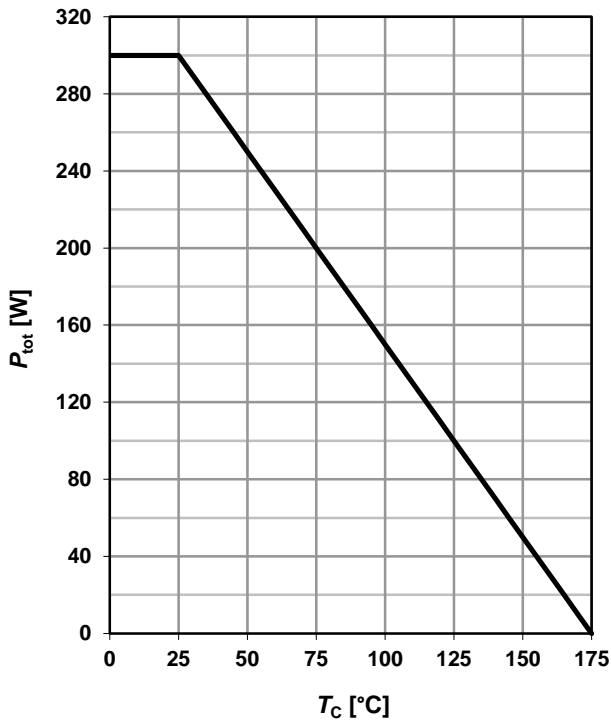
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	180	A
Diode pulse current	$I_{S,pulse}$		-	-	720	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=100\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=30\text{ V}, I_F=100\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$	-	87	139	ns
Reverse recovery charge	$Q_{rr}$		-	144	-	

<sup>5)</sup> See figure 16 for gate charge parameter definition

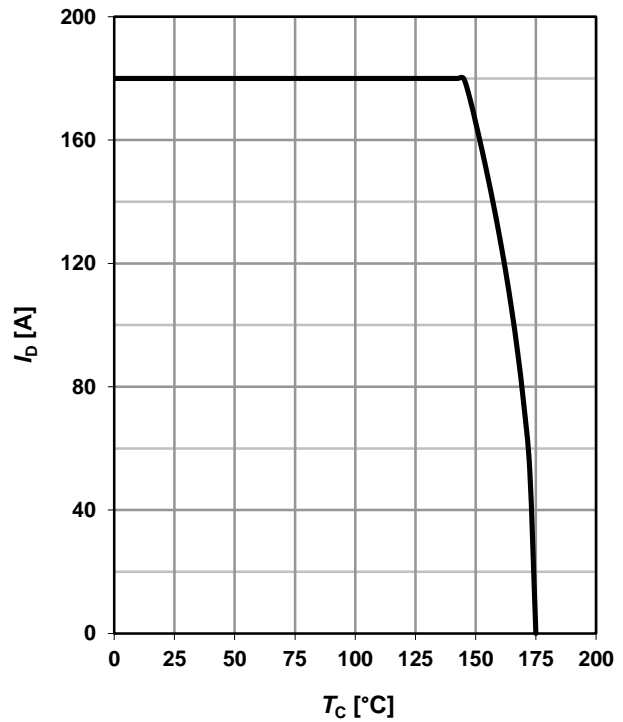
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

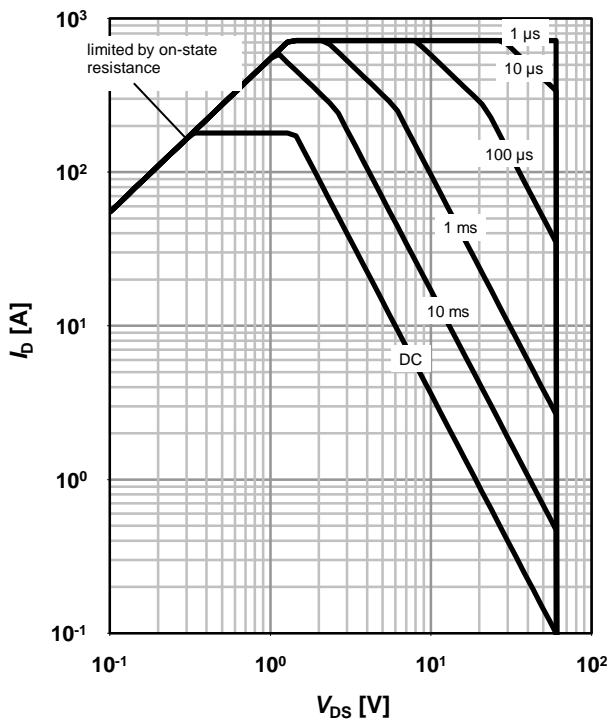
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

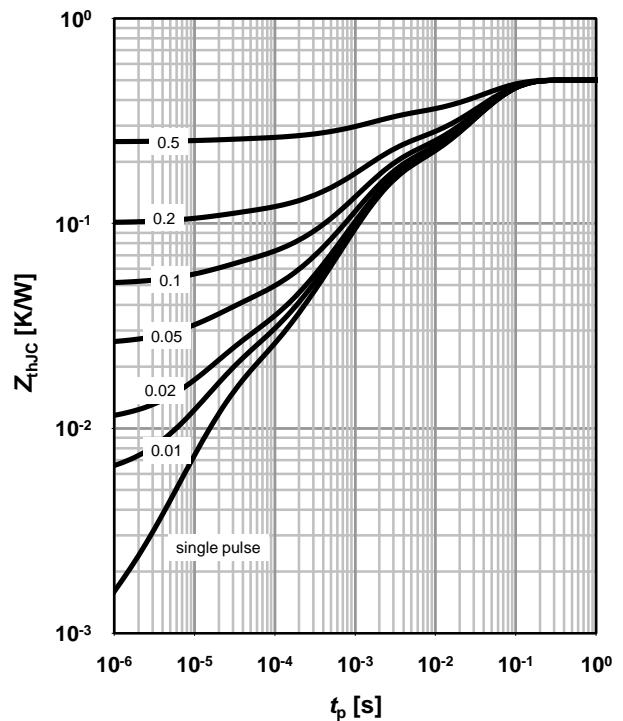
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

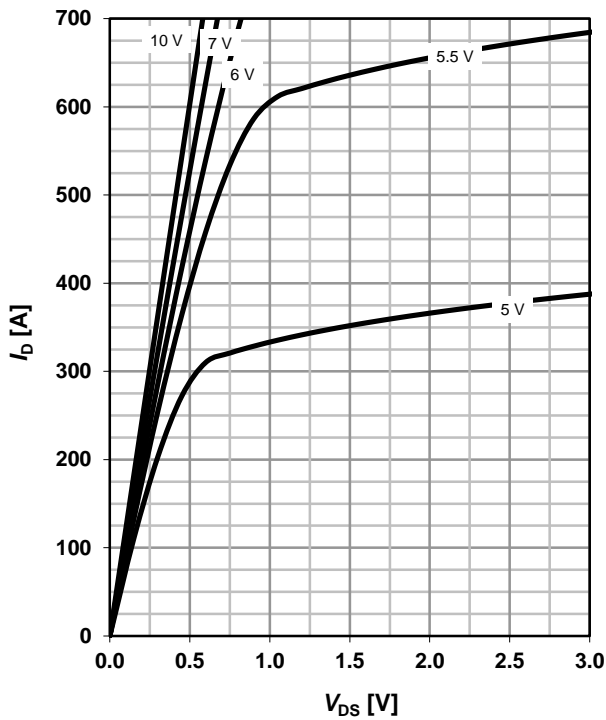
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

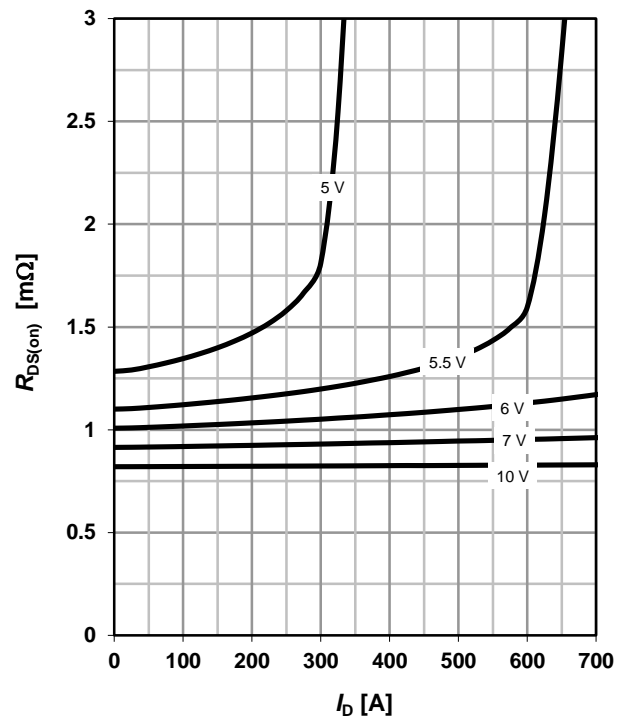
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

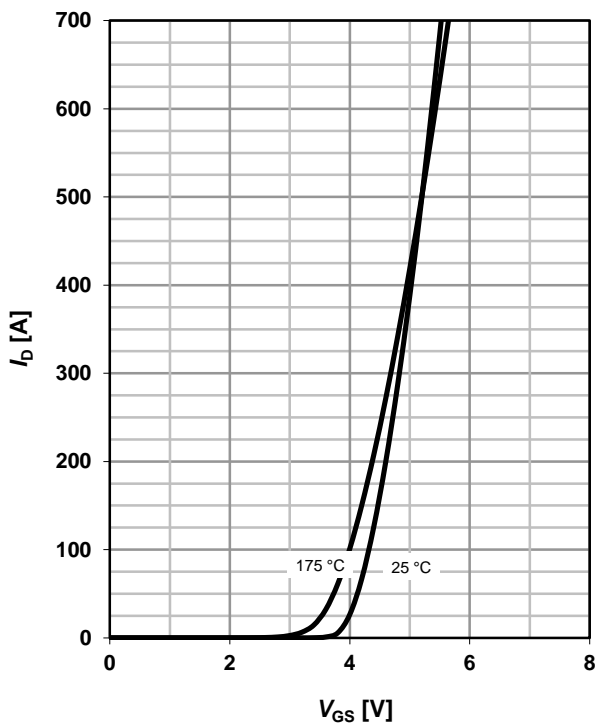
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

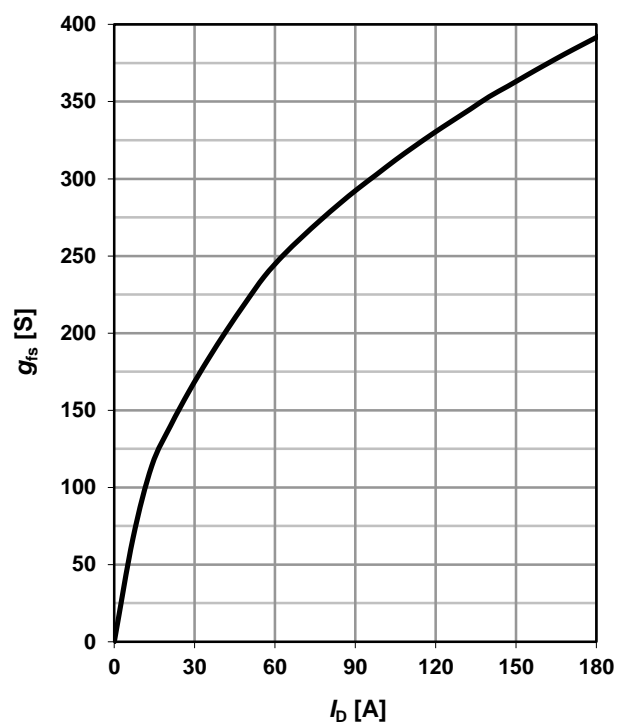
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



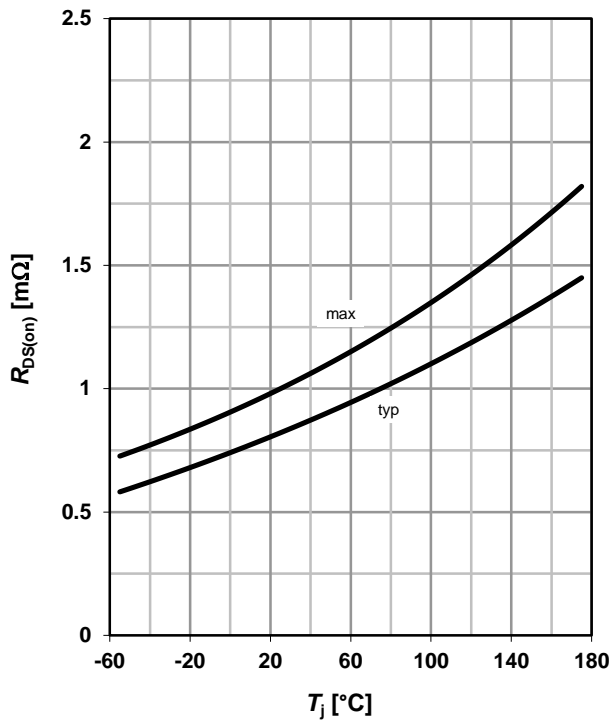
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



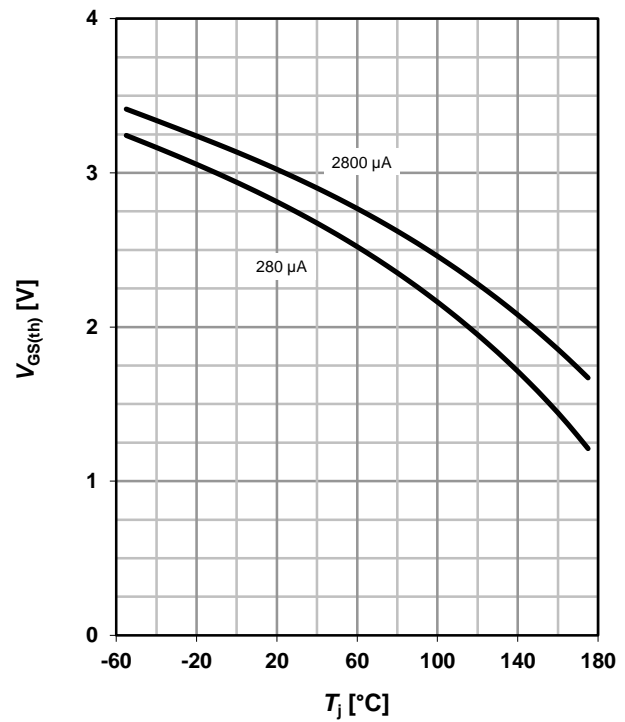
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=100\text{ A}; V_{GS}=10\text{ V}$



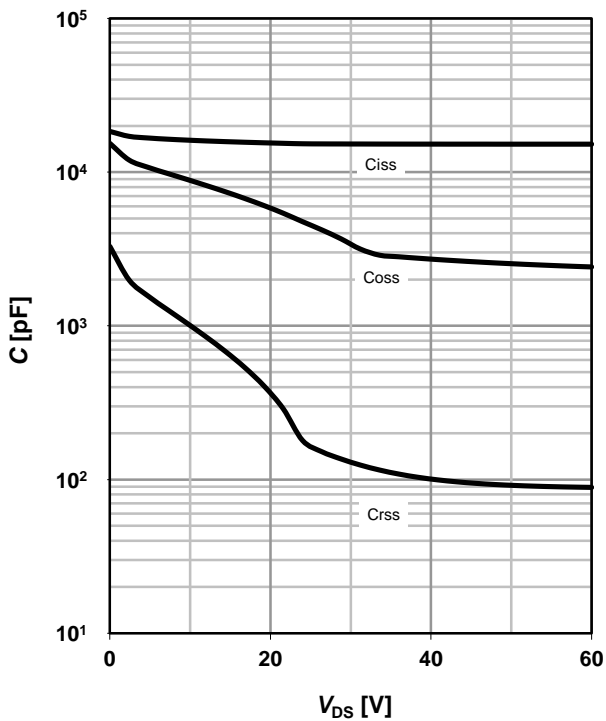
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$



**11 Typ. capacitances**

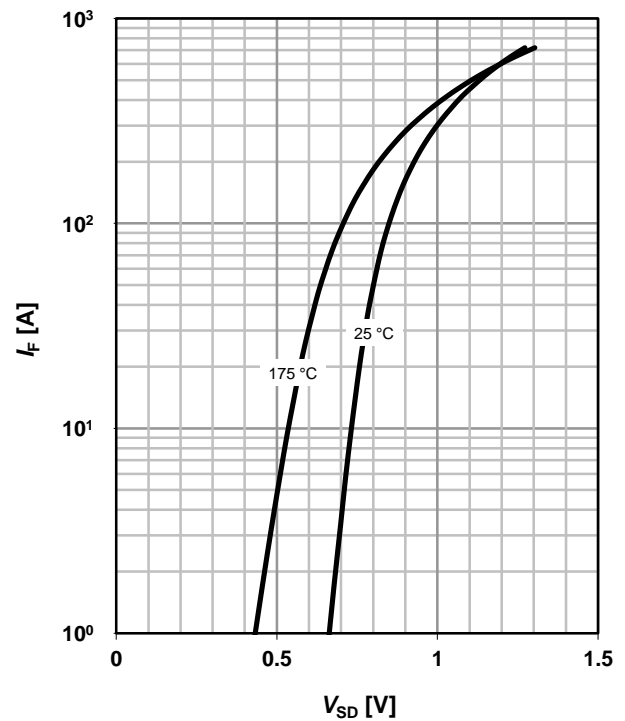
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

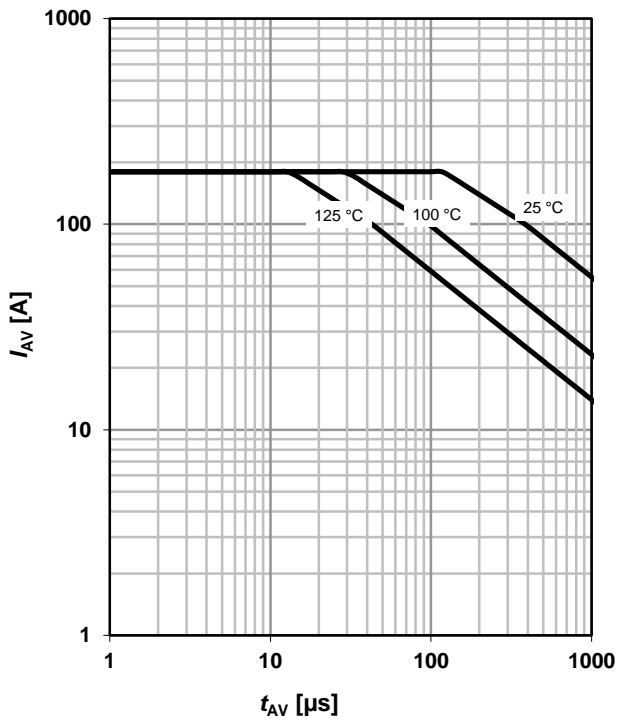
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

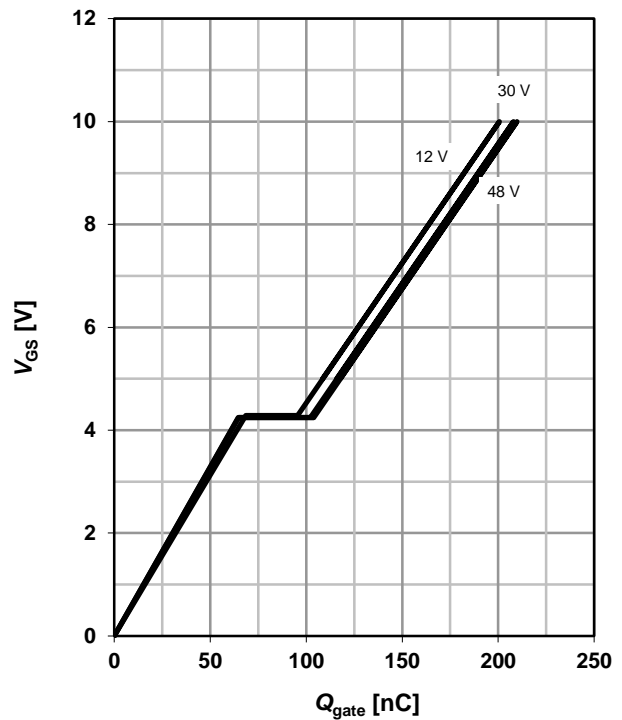
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

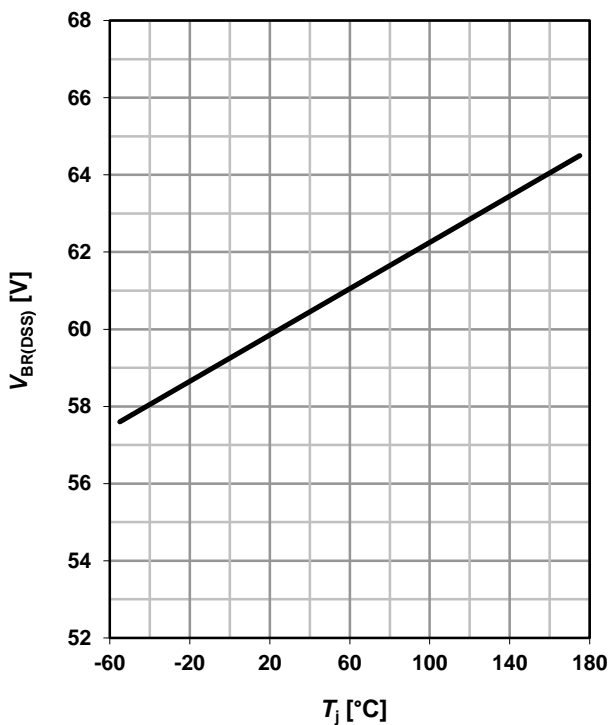
$V_{GS}=f(Q_{\text{gate}}); I_D=100 \text{ A pulsed}$

parameter:  $V_{DD}$

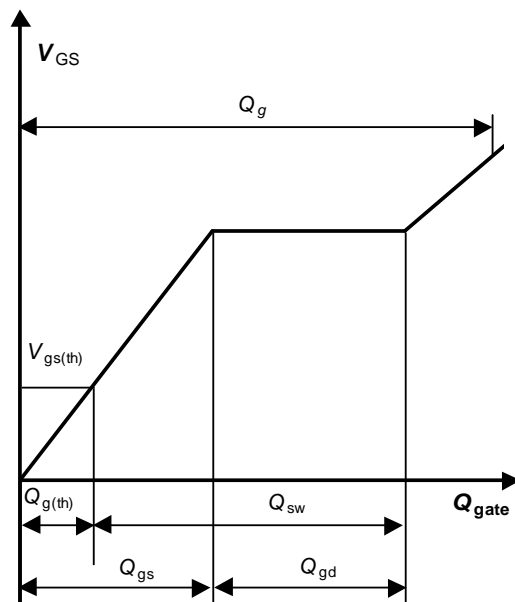


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

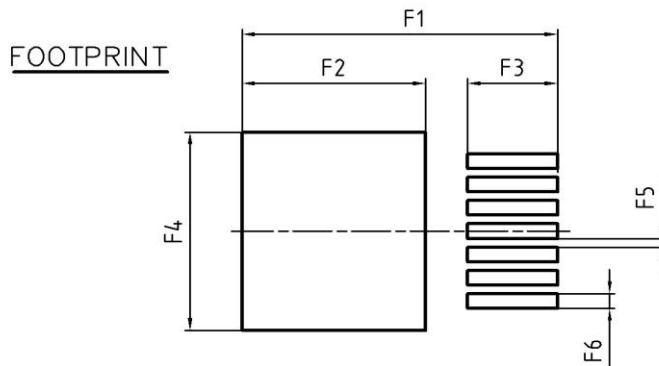
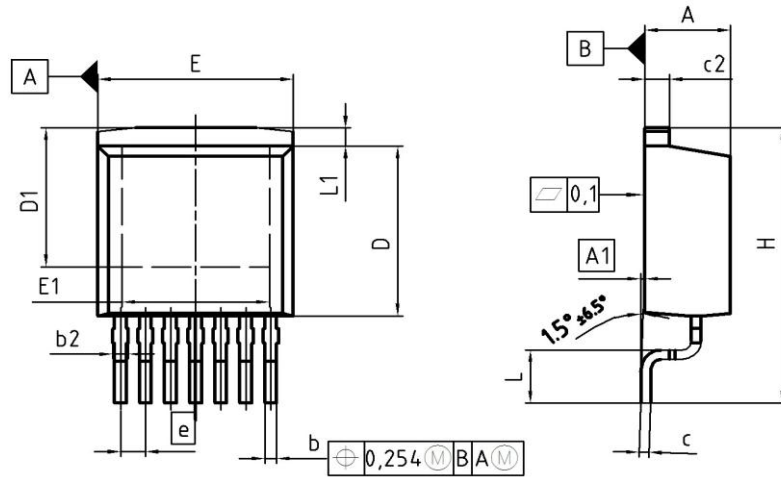


**16 Gate charge waveforms**



Package Outline

TO 263-7



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	0.00	0.25	0.000	0.010
b	0.50	0.70	0.020	0.028
b2	0.50	1.00	0.020	0.039
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.51	9.45	0.335	0.372
D1	6.90	7.90	0.272	0.311
E	9.80	10.31	0.386	0.406
E1	6.50	8.60	0.256	0.339
e	1.27		0.050	
N	7		7	
H	14.61	15.88	0.575	0.625
L	2.29	3.00	0.090	0.118
L1	0.70	1.60	0.028	0.063
F1	16.05	16.25	0.632	0.640
F2	9.30	9.50	0.366	0.374
F3	4.50	4.70	0.177	0.185
F4	10.70	10.90	0.421	0.429
F5	0.37	0.57	0.015	0.022
F6	0.70	0.90	0.028	0.035

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